

# CD914, CD3600, CD4148, CD4150, CD4153, CD4454, CD4531, CD6640, CD6642

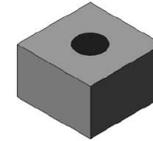


## Silicon Switching Diode Chips

Rev. V2

### Features

- All Junctions Completely Protected with Silicon Dioxide



### Description

These silicon switching diode chips are compatible with all wire bonding and die attach techniques with the exception of solder reflow.

Available in JANHC and JANKC per:

- CD914, CD4148 & CD4531: MIL-PRF-19500/116
- CD4153: MIL-PRF-19500/133
- CD6642: MIL-PRF-19500/578
- CD6640: MIL-PRF-19500/609

### Electrical Specifications: $T_A = +25^\circ\text{C}$ (unless otherwise specified)

Parameter	Test Conditions	Units	CD914	CD4148 CD4531	CD6642	CD4454
Breakdown Voltage	@ 100 mA	Volts (min)	100	100	100	75
VRWM	—	Volts (pk)	75	75	75	50
IO	—	mA	200	200	300	200
Forward Voltage1	$I_F = 10 \text{ mA}$	Vdc	0.8	0.8	0.8	1
Forward Voltage2	$I_F = 50 \text{ mA}$	Vdc	1.2	N/A	N/A	N/A
Forward Voltage3	$I_F = 100 \text{ mA}$	Vdc	N/A	1.2	1.2	N/A
Trr	—	nsec	5	5	5	4
Reverse Current1	@ 20 Vdc	nA	25	25	25	N/A
Reverse Current2	—	$\mu\text{A @ V}$	0.5 @ 75	0.5 @ 75	0.5 @ 75	0.1 @ 50
Reverse Current3	20 Vdc, $T_A = +150^\circ\text{C}$	$\mu\text{A}$	35	35	50	N/A
Reverse Current4	$T_A = +150^\circ\text{C}$	$\mu\text{A @ V}$	75 @ 75	75 @ 75	100 @ 75	100 @ 50
Capacitance	@ 0 V	pF	4	4	5	2
Capacitance	@1.5 V	pF	2.8	2.8	2.8	N/A

Parameter	Test Conditions	Units	CD3600	CD4150	CD6640	CD4153
Breakdown Voltage	$I_R = 10 \text{ mA}^1$	Volts (min)	75	75	75	100 <sup>1</sup>
VRWM	—	Volts (pk)	50	50	50	75
Reverse Current1	$V_R = 50 \text{ Vdc}$	$\mu\text{A Vdc}$	0.1	0.1	0.1	0.05
Reverse Current2	$V_R = 50 \text{ Vdc}$ , $T_A = +150^\circ\text{C}$	$\mu\text{A Vdc}$	100	100	90	50
Capacitance	$V_R = 0$ ; $f = 1 \text{ MHz}$ ; ac signals = 50 mV (p-p)	pF	2.5	2.5	2.5	2
Trr	$\mu\text{A}$	nsec	4	4	4	4

1. @ 5  $\mu\text{A}$  for CD4153

1 \* Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.

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### Forward Voltage Limits for CD3600, CD4150 and CD6640:

Parameter	Test Conditions	Limits	Minimum	Maximum
Forward Voltage1	IF = 1 mA dc (Pulsed)	Vdc	0.54	0.62
Forward Voltage2	IF = 10 mA dc (Pulsed)	Vdc	0.68	0.74
Forward Voltage3	IF = 50 mA dc (Pulsed)	Vdc	0.76	0.86
Forward Voltage4	IF = 100 mA dc (Pulsed)	Vdc	0.82	0.92
Forward Voltage5	IF = 200 mA dc (Pulsed)	Vdc	0.87	1.00

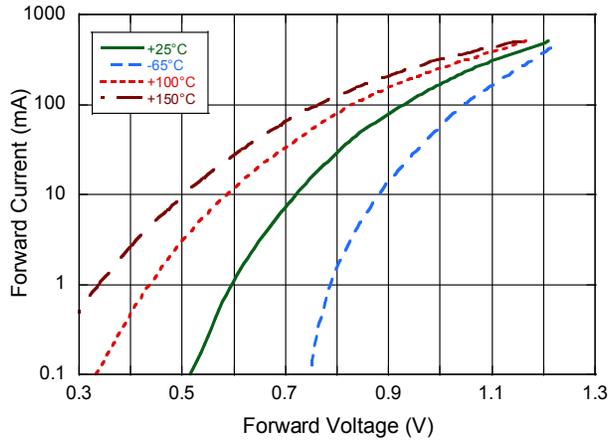
### Forward Voltage Limits for CD4153:

Parameter	Test Conditions	Limits	Minimum	Maximum
Forward Voltage1	IF = 100 $\mu$ A dc	Vdc	0.49	0.55
Forward Voltage2	IF = 250 $\mu$ A dc	Vdc	0.53	0.59
Forward Voltage3	IF = 1 mA dc	Vdc	0.59	0.67
Forward Voltage4	IF = 2 mA dc	Vdc	0.62	0.70
Forward Voltage5	IF = 10 mA dc	Vdc	0.70	0.81
Forward Voltage6	IF = 20 mA dc	Vdc	0.74	0.88

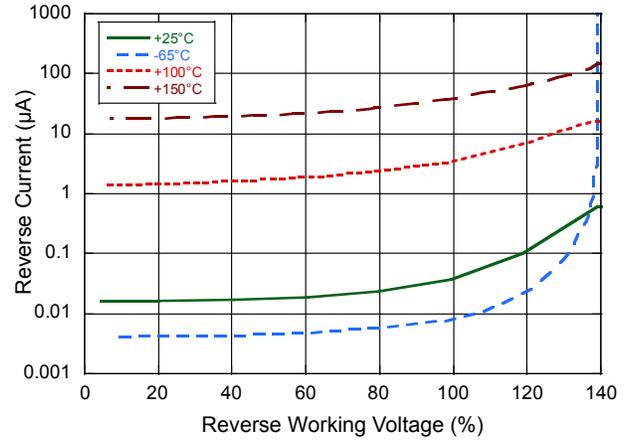
### Absolute Maximum Ratings<sup>1,2</sup>

Parameter	Absolute Maximum
Operating Temperature	-55°C to +175°C
Storage Temperature	-65°C to +175°C

**Forward Current vs. Forward Voltage**

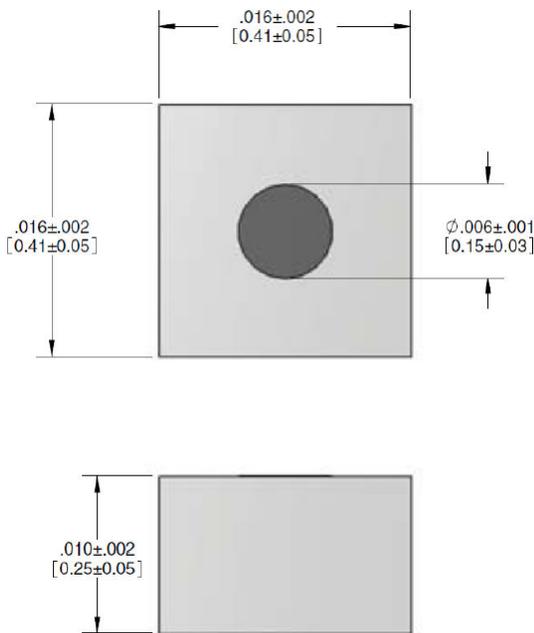


**Reverse Current vs. Reverse Voltage**



All temperature shown on graphs is junction temperature.

**Die**



Metallization: Top: (anode) AL  
Back: (cathode) Au  
AL Thickness: 25,000 Å Minimum  
Gold Thickness: 4,000 Å Minimum  
Chip Thickness: 10 mils

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